

TDSEMIC

拓電半導體

自主封測 品質把控 售後保障

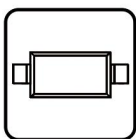
WEB | WWW.TDSEMIC.COM



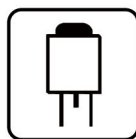
電源管理



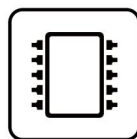
顯示驅動



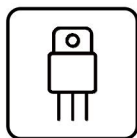
二三極管



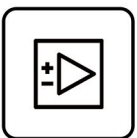
LDO穩壓器



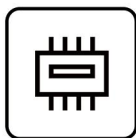
觸摸芯片



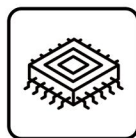
MOS管



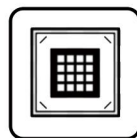
運算放大器



存儲芯片



MCU



串口通信

78M05-TD (1.5A)

產品規格說明書

FEATURES

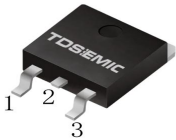
- Output Crrnt in Excess of 1.5A
- Output Voltage is 5V
- Internal thermal Overload protection
- Internal Short Circuit Current Limiting

PIN CONNECTION

1.INPUT

2. GND

3. OUTPUT



ABSOLUTE MAXIMUM RATINGS (Ta=25 °C)

Characteristics	Symbol	Value	Unit
Input Voltage	Vi	7 ~ 36	V
Storage Temperature Range	Tstg	- 85 ~ 150	°C

ELECTRICAL CHARACTERISTICS

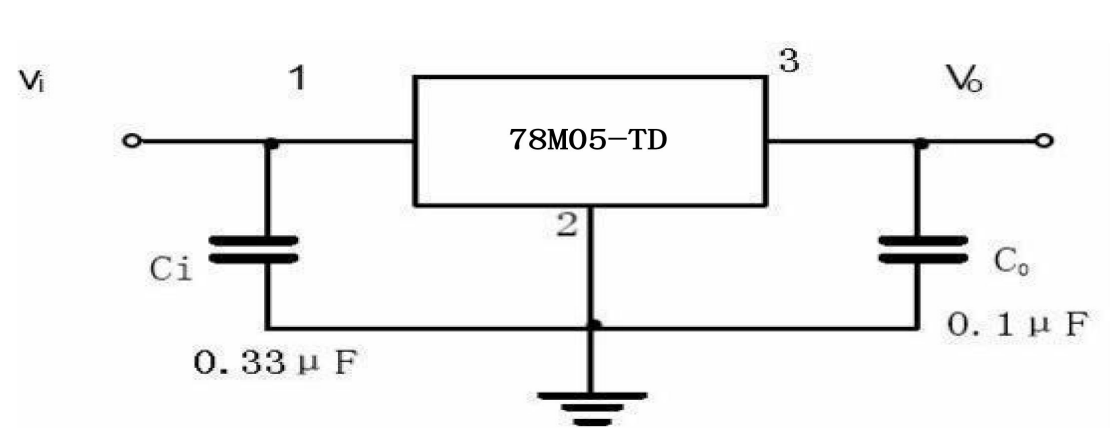
(unless otherwise noted, Vi=10V,Io=350 mA, 0 °C< Tj< 125 °C,C1= 0.33 μF,Co= 0. 1 μ F)

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Output Voltage	Vo	Tj=25 °C	4.8	5 .0	5.2	V
		7V≤Vi≤ 20 V ,Io=5mA ~ 350 mA	4.75	5	5.25	
Load Regulation	Δ Vo	Tj=25 °C ,Io=5mA ~ 1000mA		25	100	mV
		Tj=25 °C ,Io=5mA ~ 200mA		10	50	
Line Regulation	Δ Vo	7V≤Vi≤ 25 V,Io=300mA, Tj=25 °C		4	100	mV
		8V≤Vi≤ 25 V,Io=300mA, Tj=25 °C		2	50	
Quiescent Current	Iq	Tj=25 °C		4	6	m A
Quiescent Current Charge	ΔIq	8V≤Vi≤ 25 V,Io=300mA			0.8	mA
		5mA≤Io≤ 350 mA			0.5	

Continues:

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Output Noise Voltage	V_N	$10\text{Hz} \leq f \leq 100\text{kHz}$, $T_j = 25^\circ\text{C}$		40	200	μV
Dropout Voltage	V_d	$T_j = 25^\circ\text{C}$		1.7		V
Ripple Rejection	RR	$8\text{V} \leq V_i \leq 18\text{V}$, $f = 120\text{Hz}$, $I_o = 300\text{mA}$, $T_j = 25^\circ\text{C}$	56	80		dB
Short Circuit Current Limit	I_{sc}	$T_j = 25^\circ\text{C}$		950		mA

APPLICATION CIRCUIT



*Bypass capacitors are recommended for optimum stability and transient response and should be located as close as Possible to the regulators.

OUTLINE DRAWING

